



2SA1479/2SC3789

High-Definition CRT Display Video Output Applications

Applications

- High-definition CRT display.
- Color TV chroma output, high breakdown voltage drivers.

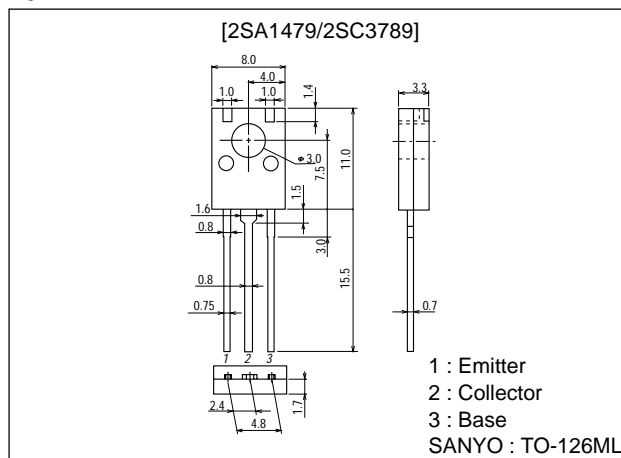
Features

- High breakdown voltage ($V_{CEO} \geq 300V$).
- Excellent high frequency characteristic
: $C_{re} = 1.8pF$ (typ).
- Adoption of MBIT process.
- No insulator required for mounting, which contributes to reducing the cost and the number of manufacturing processes.
- Plastic-covered heat sink facilitating high-density mounting.
- Directly interchangeable with TO-126 because the package is designed based on the conventional package dimensions.

Package Dimensions

unit:mm

2042B



(): 2SA1479

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)300	V
Collector-to-Emitter Voltage	V_{CEO}		(-)300	V
Emitter-to-Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)100	mA
Peak Collector Current	I_{CP}		(-)200	mA
Collector Dissipation	P_C		1.5	W
		$T_c = 25^\circ C$	7	W
Junction Temperature	T_J		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

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SANYO Electric Co., Ltd. Semiconductor Company

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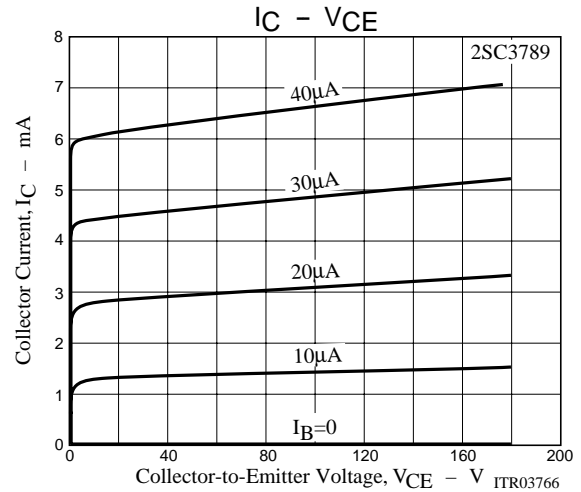
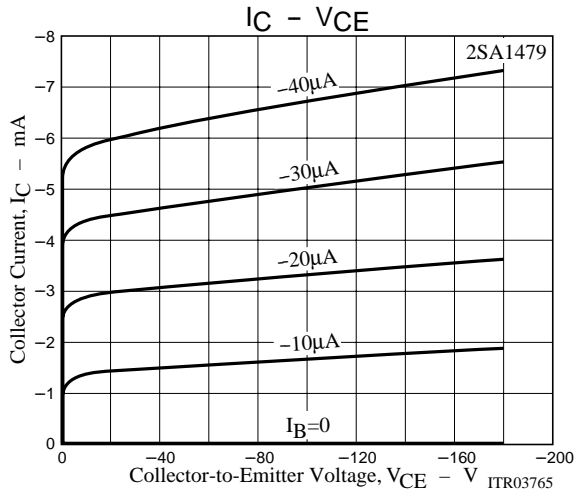
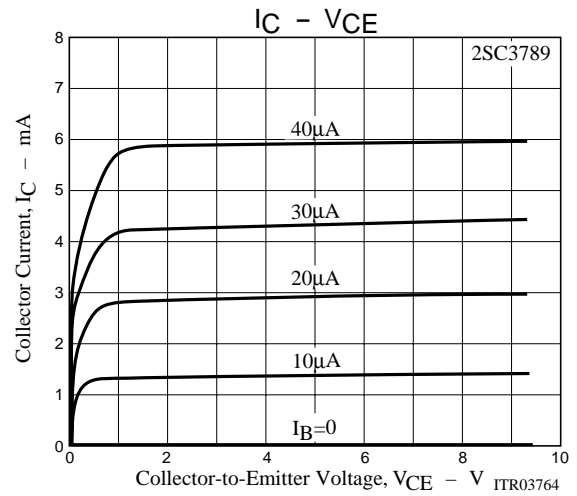
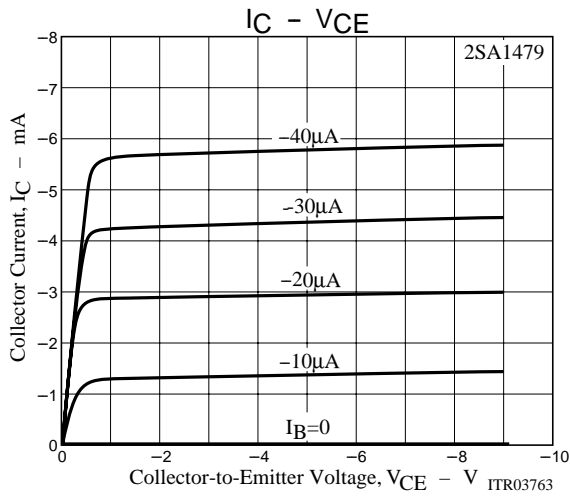
2SA1479/2SC3789

Electrical Characteristics at $T_a = 25^\circ\text{C}$

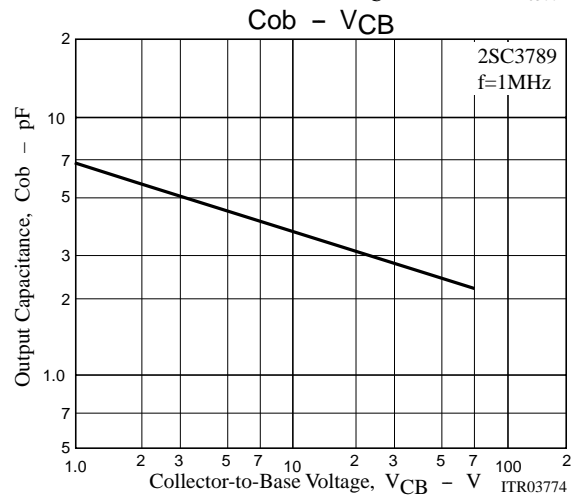
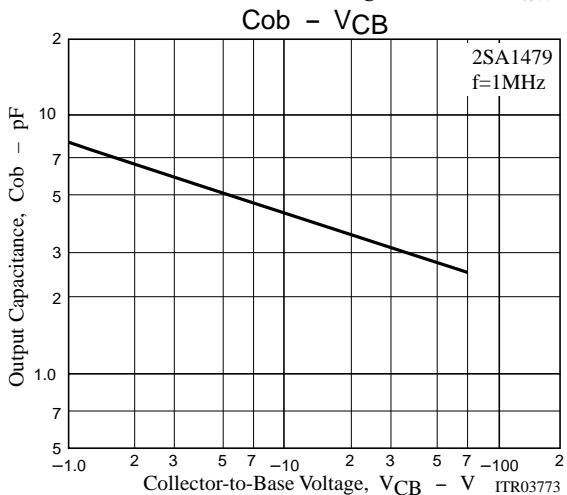
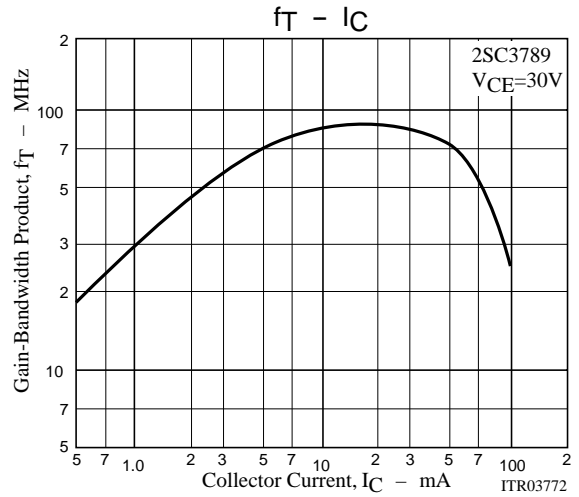
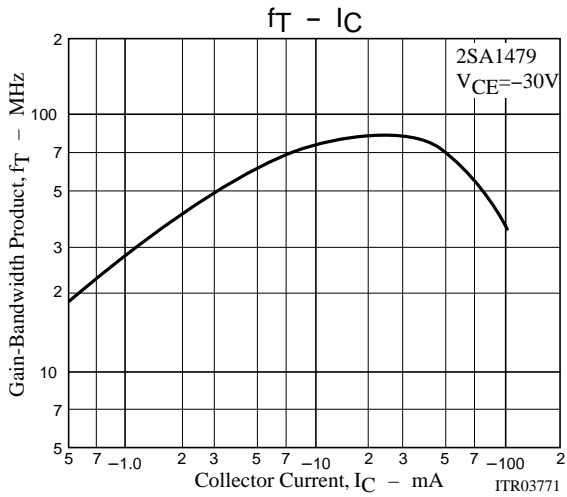
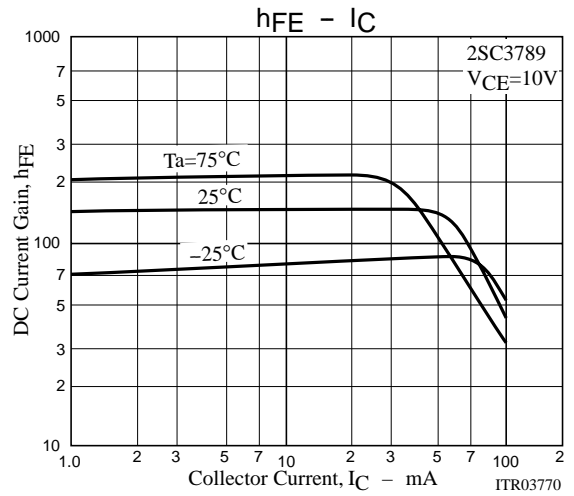
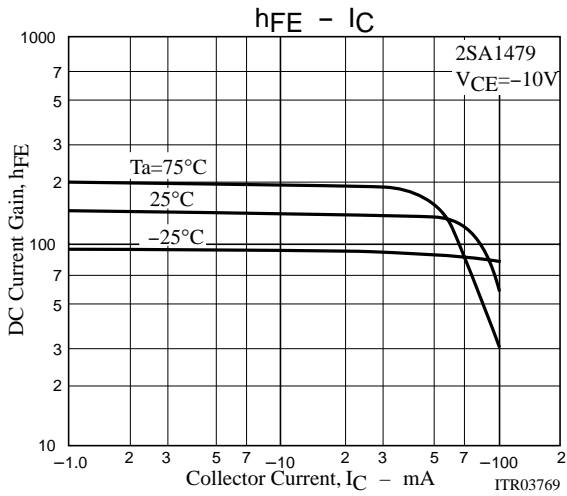
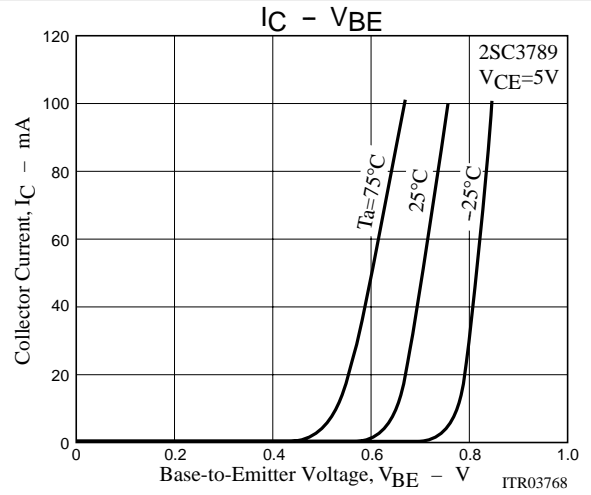
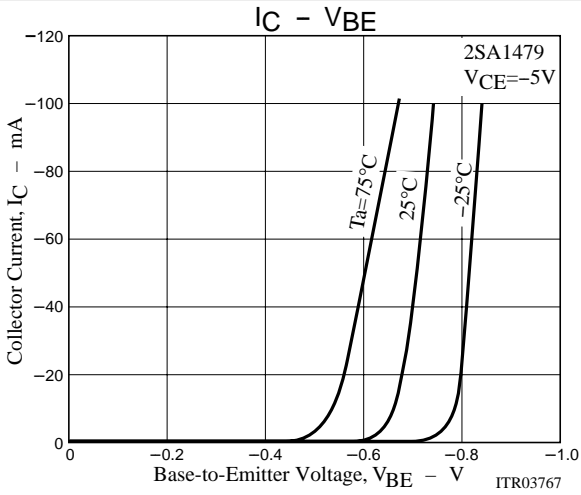
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)200\text{V}, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)10\text{V}, I_C=(-)10\text{mA}$	40*		320*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)30\text{V}, I_C=(-)10\text{mA}$		70		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)20\text{mA}, I_B=(-)2\text{mA}$			(-)0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)20\text{mA}, I_B=(-)2\text{mA}$			(-)1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)300			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)300			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)5			V
Output Capacitance	C_{ob}	$V_{CB}=(-)30\text{V}, f=1\text{MHz}$		2.6		pF
				(3.1)		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=(-)30\text{V}, f=1\text{MHz}$		1.8		pF
				(2.3)		pF

* : The 2SA1479/2SC3789 are classified by 10mA h_{FE} as follows :

Rank	C	D	E	F
h_{FE}	40 to 80	60 to 120	100 to 200	160 to 320



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